

Vishay Semiconductors

HALOGEN

FREE

Infrared Emitting Diode, 950 nm, GaAs



DESCRIPTION

TSUS5400 is an infrared, 950 nm emitting diode in GaAs technology molded in a blue-gray tinted plastic package.

FEATURES

Package type: leaded
Package form: T-1¾
Dimensions (in mm): Ø 5
Leads with stand-off

• Peak wavelength: $\lambda_p = 950 \text{ nm}$

· High reliability

• Angle of half intensity: $\phi = \pm 22^{\circ}$

· Low forward voltage

• Suitable for high pulse current operation

· Good spectral matching with Si photodetectors

 Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

• Halogen-free according to IEC 61249-2-21 definition

APPLICATIONS

- Infrared remote control and free air transmission systems with low forward voltage and small package requirements
- · Emitter in transmissive sensors
- · Emitter in reflective sensors

PRODUCT SUMMARY						
COMPONENT	I _e (mW/sr)	φ (deg)	λ _P (nm)	t _r (ns)		
TSUS5400	14	± 22	950	800		
TSUS5401	17	± 22	950	800		
TSUS5402	20	± 22	950	800		

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION						
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM			
TSUS5400	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾			
TSUS5401	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾			
TSUS5402	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾			

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT		
Reverse voltage		V _R	5	V		
Forward current		I _F	150	mA		
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I _{FM}	300	mA		
Surge forward current	t _p = 100 μs	I _{FSM}	2.5	Α		
Power dissipation		P _V	170	mW		
Junction temperature		Tj	100	°C		
Operating temperature range		T _{amb}	- 40 to + 85	°C		
Storage temperature range		T _{stg}	- 40 to + 100	°C		
Soldering temperature	$t \le 5$ s, 2 mm from case	T _{sd}	260	°C		
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R _{thJA}	230	K/W		

Note

T_{amb} = 25 °C, unless otherwise specified

TSUS5400, TSUS5401, TSUS5402

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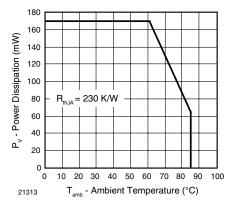


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

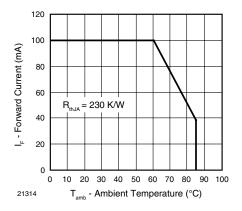


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS							
PARAMETER	TEST CONDITION	SYMBOL MIN.		TYP.	MAX.	UNIT	
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V _F		1.3	1.7	V	
Temperature coefficient of V _F	I _F = 100 mA	TK _{VF}		- 1.3		mV/K	
Reverse current	V _R = 5 V	I _R			100	μΑ	
Junction capacitance	$V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$	C _j		30		pF	
Temperature coefficient of φ _e	I _F = 20 mA	TKφe		- 0.8		%/K	
Angle of half intensity		φ		± 22		deg	
Peak wavelength	I _F = 100 mA	λ_{p}		950		nm	
Spectral bandwidth	I _F = 100 mA	Δλ		50		nm	
Temperature coefficient of λ_p	I _F = 100 mA	$TK\lambda_p$		0.2		nm/K	
	I _F = 100 mA	t _r		800		ns	
Rise time	I _F = 1.5 A	t _r		400		ns	
Fall time	I _F = 100 mA	t _f		800		ns	
Fall time	I _F = 1.5 A	t _f		400		ns	
Virtual source diameter		d		2.9		mm	

Note

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TYPE DEDICATED CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 1.5 A, t _p = 100 μs	TSUS5400	V_{F}		2.2	3.4	V
		TSUS5401	V_{F}		2.2	3.4	V
		TSUS5402	V_{F}		2.2	2.7	V
		TSUS5400	l _e	7	14	35	mW/sr
	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	TSUS5401	l _e	10	17	35	mW/sr
Padient intensity		TSUS5402	l _e	15	20	35	mW/sr
Radiant intensity		TSUS5400	l _e	60	140		mW/sr
	$I_F = 1.5 \text{ A}, t_p = 100 \ \mu \text{s}$	TSUS5401	l _e	85	160		mW/sr
		TSUS5402	I _e	120	190		mW/sr
	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	TSUS5400	фe		13		mW
Radiant power		TSUS5401	фe		14		mW
		TSUS5402	фe		15		mW

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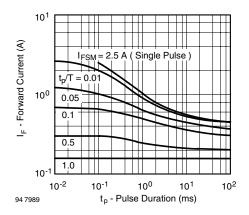


Fig. 3 - Pulse Forward Current vs. Pulse Duration

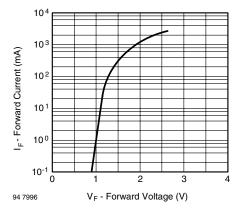


Fig. 4 - Forward Current vs. Forward Voltage

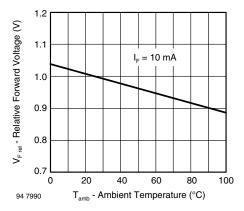


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

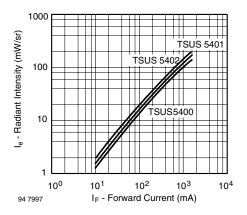


Fig. 6 - Radiant Intensity vs. Forward Current

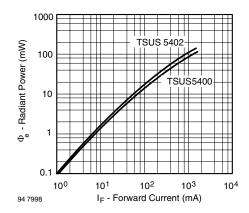


Fig. 7 - Radiant Power vs. Forward Current

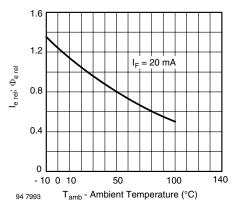


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

TSUS5400, TSUS5401, TSUS5402

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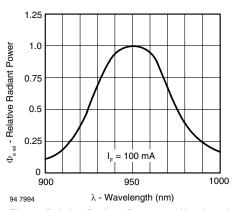


Fig. 9 - Relative Radiant Power vs. Wavelength

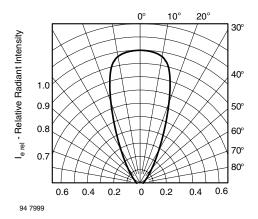
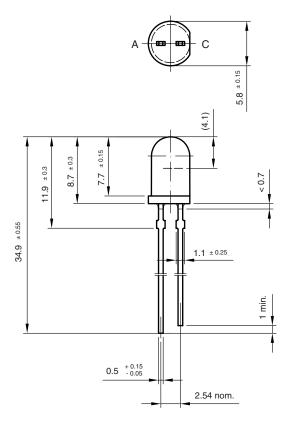
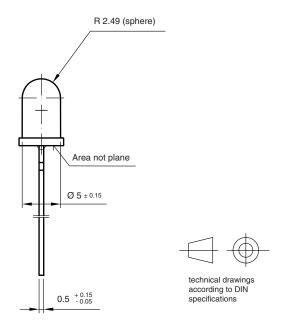


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



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